



TO-251 (IPAK) TO-252 (DPAK)

Pin Definition:
1. Gate

Drain
 Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)
500	0.85 @ V _{GS} =10V	7.2

Features

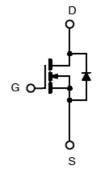
- Low On-Resistance.
- High power and current handing capability.

Ordering Information

Part No.	Package	Packing
TSM8N50CH C5G	TO-251	75pcs / Tube
TSM8N50CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: "G" denotes for Halogen Free

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Tc = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	500	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	Tc = 25°C	- I _D	7.2	А
	Tc = 100°C		4.3	А
Pulsed Drain Current (Note 1)		I _{DM}	28.8	А
Single Pulse Avalanche Energy (Note 2)		E _{AS}	181	mJ
Total Power Dissipation @ T _C = 25°C		P _{TOT}	89	W
Operating Junction Temperature		TJ	150	∘C
Storage Temperature Range		T _{STG}	-55 to +150	°C

Note1: Repetitive Rating : Pulse width limited by maximum junction temperature.

Note2: L=7mH, I_{AS} =8A, V_{DD} = 50V, V_{DS} = 200V, Starting T_J = 25 $^{\circ}$ C

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Case	R⊖ _{JC}	1.4	°C/W	
Thermal Resistance - Junction to Ambient	RO _{JA}	50		





Electrical Specifications (Tc = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	500			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 3.6A$	R _{DS(ON)}		0.7	0.85	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V _{GS(TH)}	2.0	3.0	4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic (Note a)						
Total Gate Charge		Q_g		26.6		nC
Gate-Source Charge	$V_{DD} = 400V, I_D = 7A,$	Q_{gs}		5.4		
Gate-Drain Charge	$V_{GS} = 10V$	Q_{gd}		6.82		
Input Capacitance		C _{iss}		1595		pF
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		127.4		
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		14.5		
Switching (Note a)						
Turn-On Delay Time		t _{d(on)}		22		
Turn-On Rise Time	$V_{GS} = 10V, I_{D} = 7A,$	t _r		6.8		
Turn-Off Delay Time	$V_{DD} = 250V, R_{GEN} = 9.1\Omega$	t _{d(off)}		42		nS
Turn-Off Fall Time		t _f		4.8		
Source-Drain Diode Ratings and C	haracteristic					
Source Current		I _S			7	Α
Diode Forward Voltage	$I_S = 7A$, $V_{GS} = 0V$	V_{SD}			1.5	V

Note a: Pulse Test : Pulse Width < 300µs, Duty Cycle < 2%.

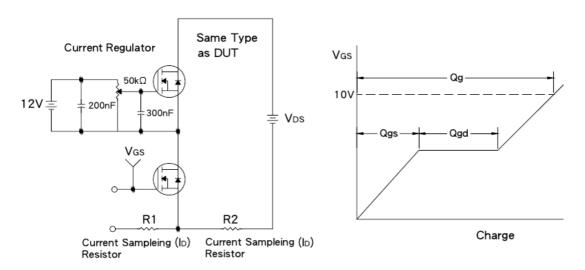


TSM8N50

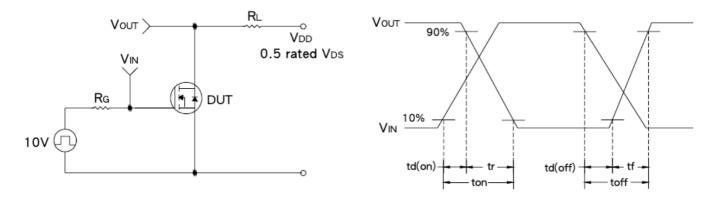
500V N-Channel MOSFET



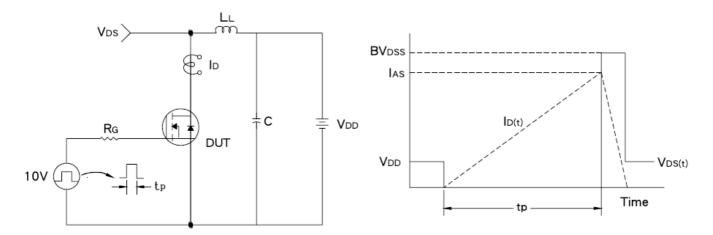
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



EAS Test Circuit & Waveform

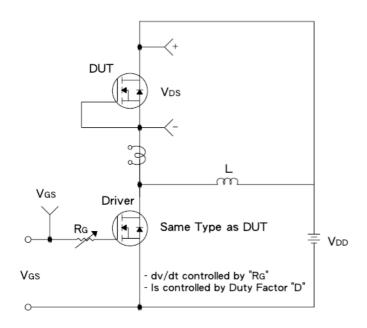


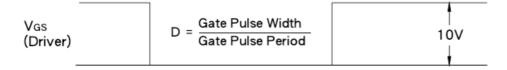
TSM8N50

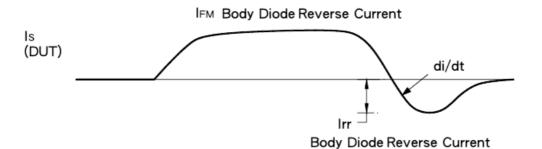
500V N-Channel MOSFET

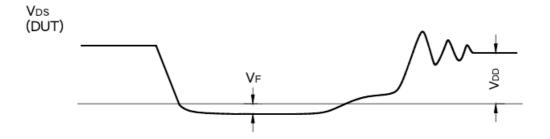


Diode Reverse Recovery Time Test Circuit & Waveform



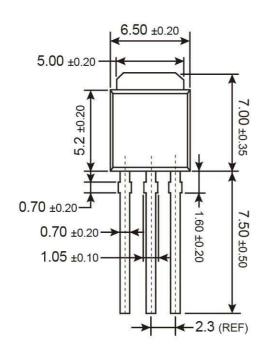


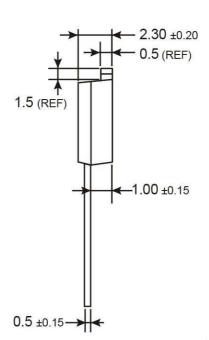






TO-251 Mechanical Drawing

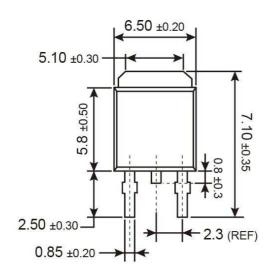


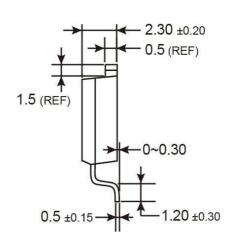


Unit: Millimeters



TO-252 Mechanical Drawing





Unit: Millimeters



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